

ABSTRACTINTEGRATED SEMICONDUCTOR CIRCUIT COMPRISING A
TRANSISTOR AND A STRIP CONDUCTOR

The invention relates to an integrated semiconductor circuit comprising a transistor and an interconnect (11), the transistor exhibiting a first (1) and a second source/drain electrode (2) and a gate electrode, the interconnect (11) being electrically insulated from a semiconductor substrate at least by a gate dielectric and forming the gate electrode in the area of the transistor and the interconnect (11) extending along a first direction (x) in the area of the transistor. According to the invention, it is provided that the second source/drain electrode (2) is arranged offset with respect to the first source/drain electrode (1) in the first direction (x). The transistor thus formed has an inversion channel (K1) which only extends between two corner areas (1a, 2a) facing one another of the first and of the second source/drain electrode, i.e. is much narrower than in the case of a conventional transistor. This makes it possible to produce more compact semiconductor circuits.

Figure 5



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